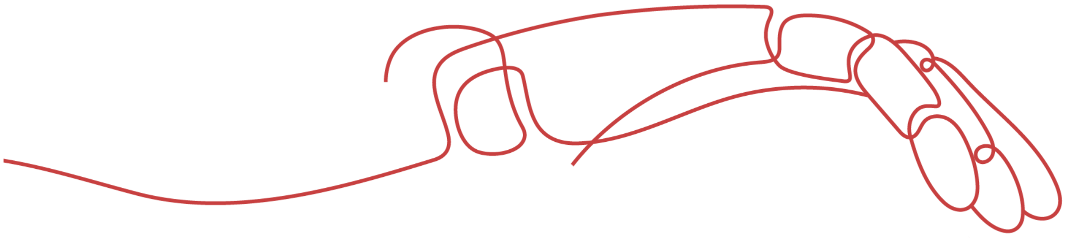
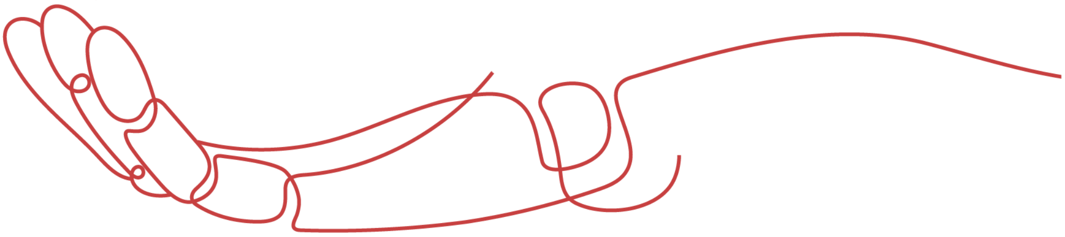


PRODUCT DATA SHEET



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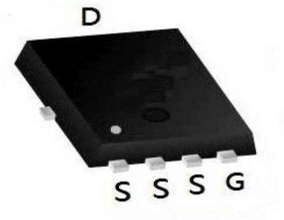
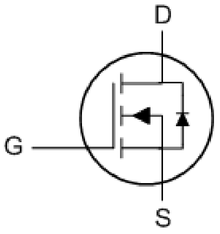
Datasheet Resources Samples

BVDSS	RDSON	ID
40V	0.75mΩ	225A



PDFN5060-8L



Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V[1,6]	225	A
I_D@T_C=100˚C	Continuous Drain Current, V_{GS} @ 10V[1,6]	141	A
I_{DM}	Pulsed Drain Current[2]	900	A
EAS	Single Pulse Avalanche Energy[3]	627.2	mJ
I_{AS}	Avalanche Current	56	A
P_D@T_C=25˚C	Total Power Dissipation[4]	114	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{θJA}$	Thermal Resistance Junction-Ambient [1]	---	50	˚C/W
$R_{θJC}$	Thermal Resistance Junction-Case[1]	---	1.1	˚C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
△BV_{DSS}/△T_J	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=17A	---	0.75	1	mΩ
		V_{GS}=4.5V , I_D=8A	---	1.05	1.4	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.7	2.4	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=40V, V_{GS}=0V , T_J=100℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=17A	---	105	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.2	---	Ω
Q_g	Total Gate Charge	V_{DS}=20V , V_{GS}=10V , I_D=17A	---	118	---	nC
Q_{gs}	Gate-Source Charge		---	19	---	
Q_{gd}	Gate-Drain Charge		---	22.2	---	
$T_{d(on)}$	Turn-On Delay Time	V_{GS}=10V, V_{DD}=20V, I_D=17A, R_{GEN}=3Ω	---	13.8	---	ns
T_r	Rise Time		---	14	---	
$T_{d(off)}$	Turn-Off Delay Time		---	91	---	
T_f	Fall Time		---	43	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	6650	---	pF
C_{oss}	Output Capacitance		---	1495	---	
C_{rss}	Reverse Transfer Capacitance		---	103	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	225	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=17A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=17A , di/dt=100A/μs , T_J=25℃	---	66	---	nS
Q_{rr}	Reverse Recovery Charge		---	39.6	---	nC

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
2. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.4mH, I_{AS}=56A.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test..

Typical Characteristics

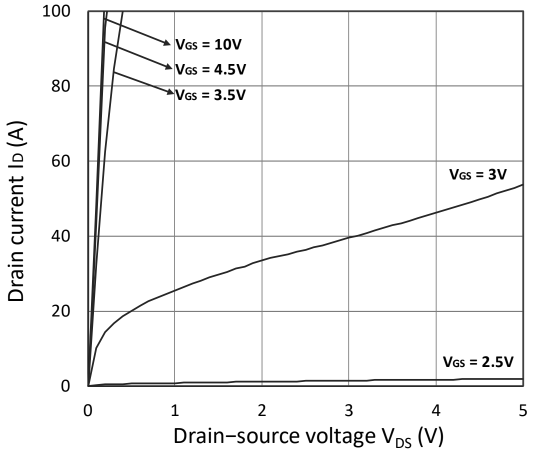


Figure 1. Output Characteristics

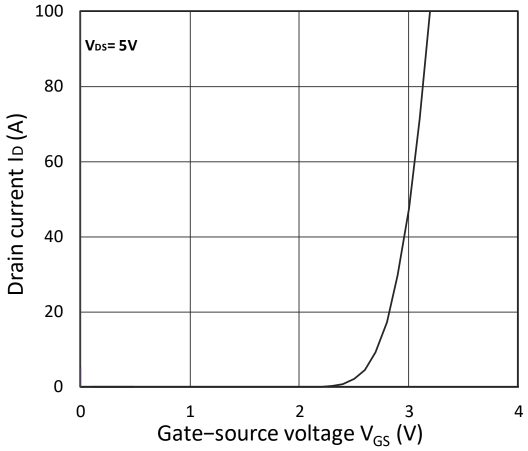


Figure 2. Transfer Characteristics

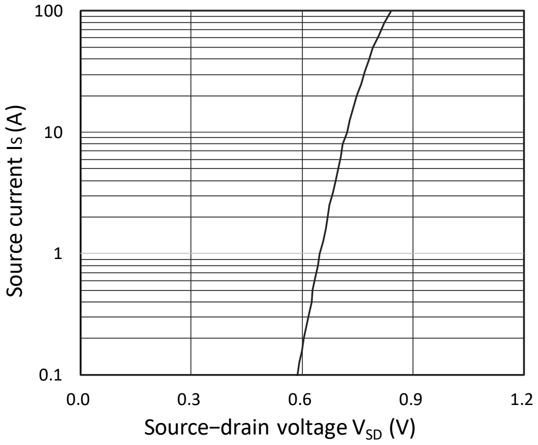


Figure 3. Forward Characteristics of Reverse

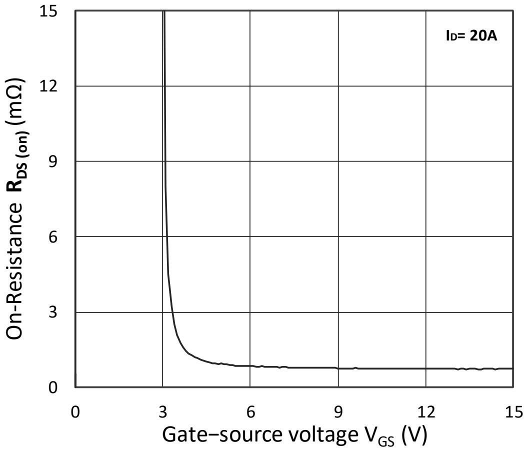


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

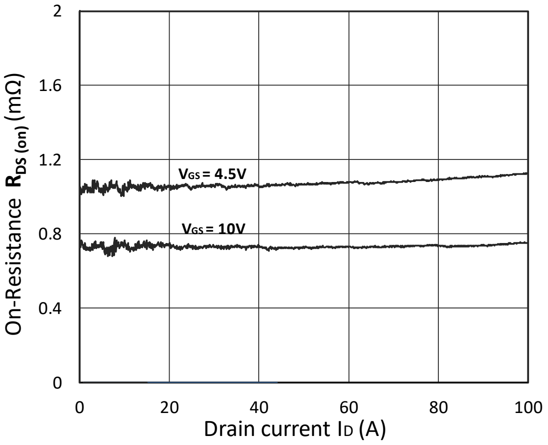


Figure 5. $R_{DS(ON)}$ vs. I_D

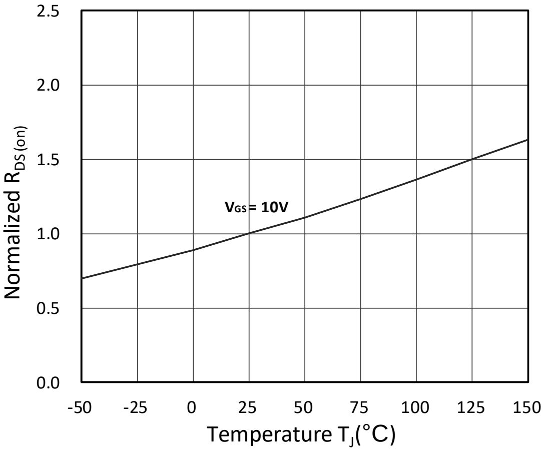


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

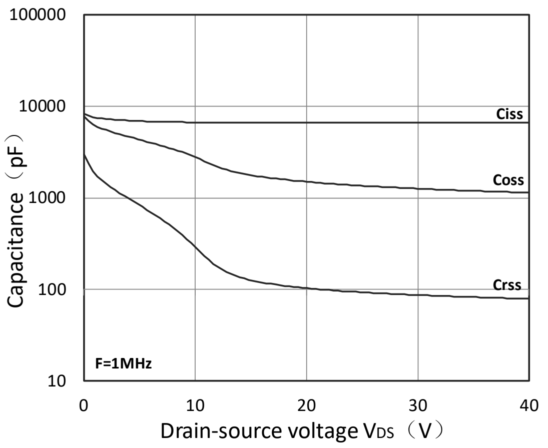


Figure 7. Capacitance Characteristics

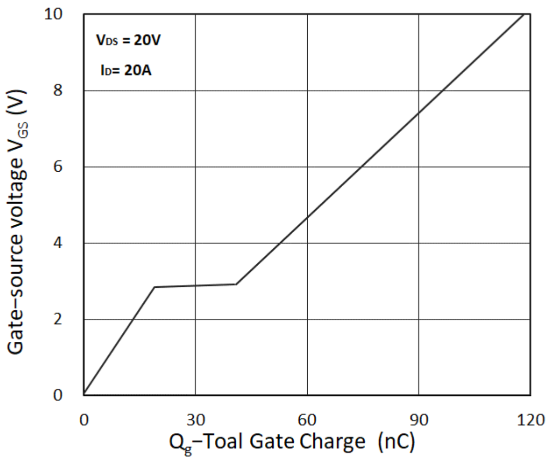


Figure 8. Gate Charge Characteristics

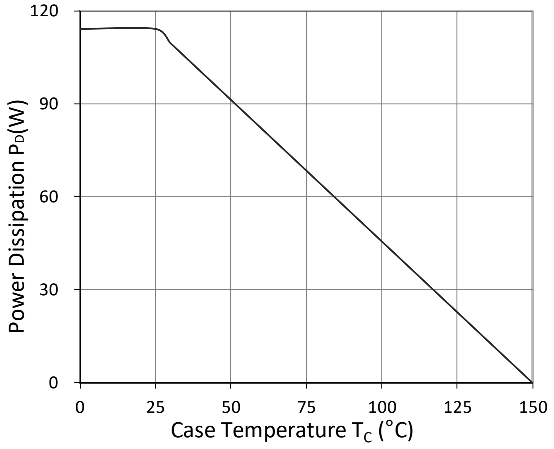


Figure 9. Power Dissipation

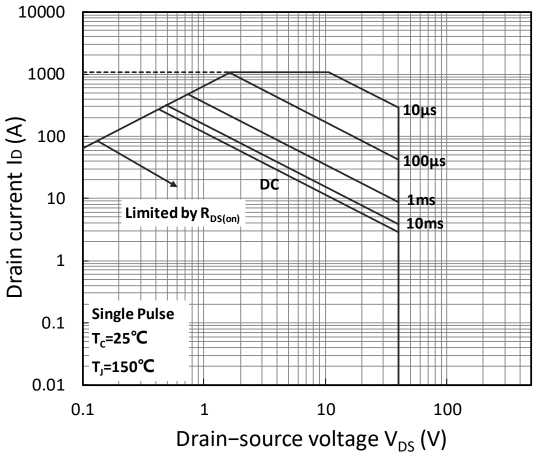


Figure10. Safe Operating Area

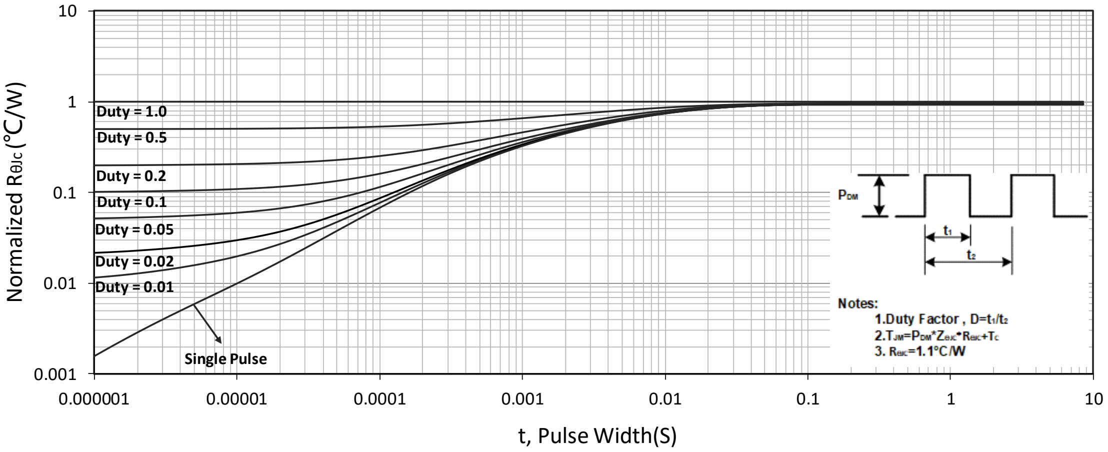


Figure 11. Normalized Maximum Transient Thermal Impedance

■ Test circuits and waveforms

Figure A: Gate Charge Test Circuit & Waveforms

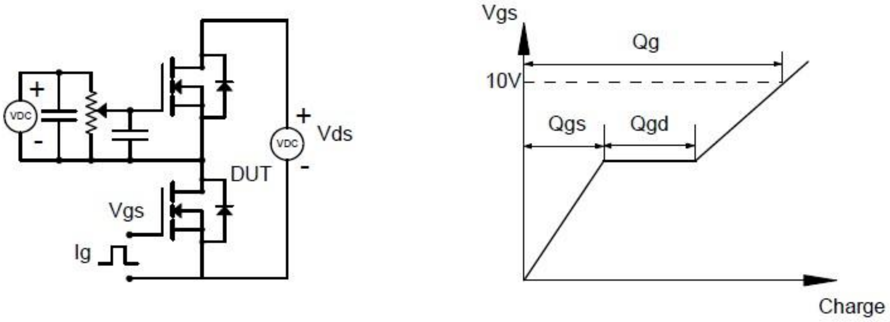


Figure B: Resistive Switching Test Circuit & Waveforms

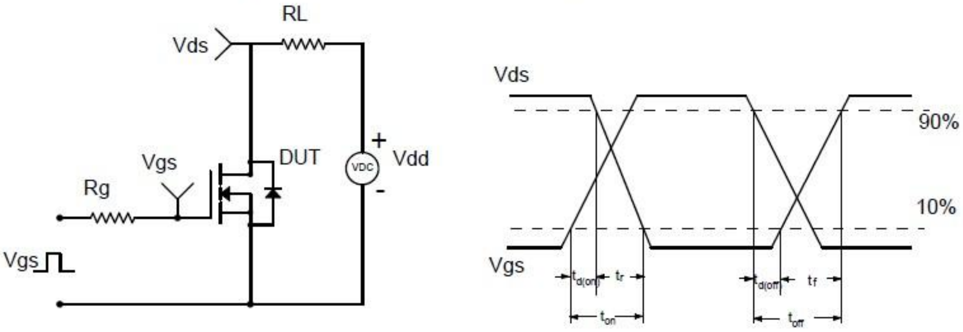


Figure C: Unclamped Inductive Switching (UIS) Test

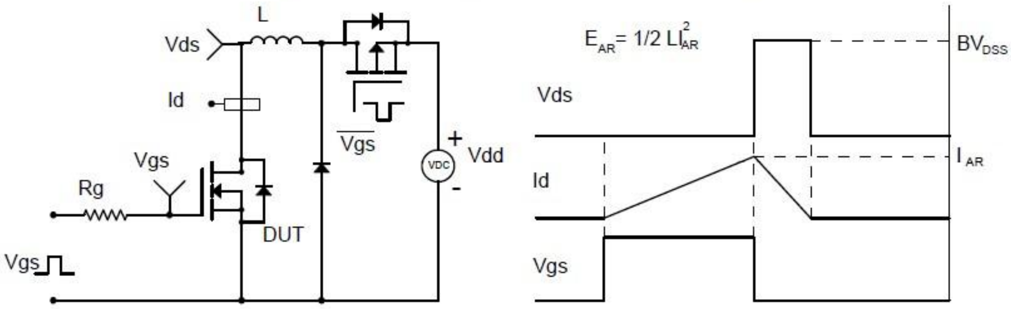
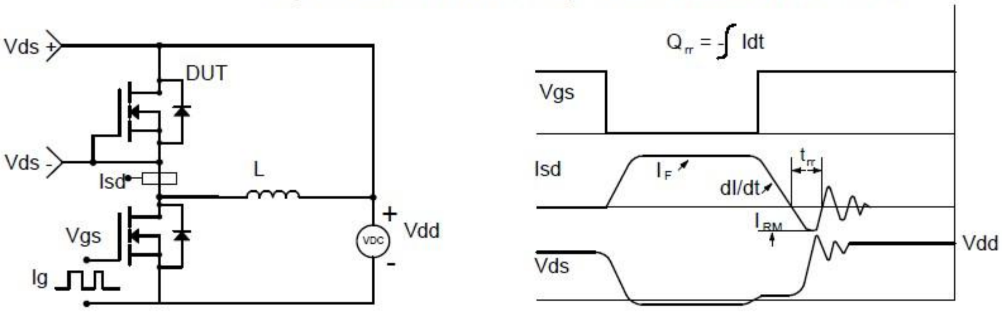
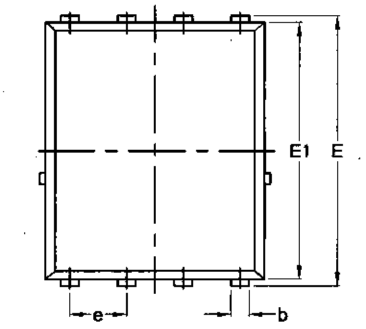
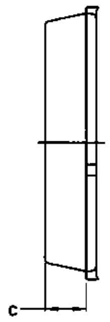


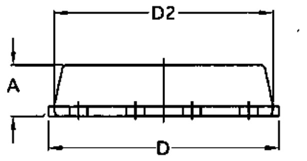
Figure D: Diode Recovery Test Circuit & Waveforms

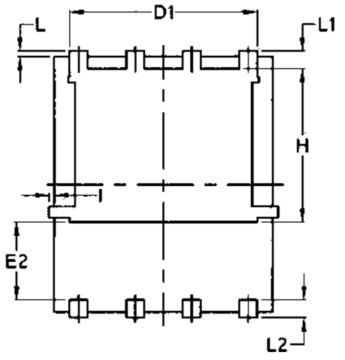


Package Mechanical Data-PDFN5060-8L-JQ Single









Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

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